

SILICON TRANSISTOR ARRAY

μPA1436

NPN SILICON POWER TRANSISTOR ARRAY LOW SPEED SWITCHING USE (DARLINGTON TRANSISTOR) INDUSTRIAL USE

DESCRIPTION

The μ PA1436 is NPN silicon epitaxial Darlington Power Transistor Array that built in 4 circuits designed for driving solenoid, relay, lamp and so on.

FEATURES

- · Easy mount by 0.1 inch of terminal interval.
- High hee for Darlington Transistor.

ORDERING INFORMATION

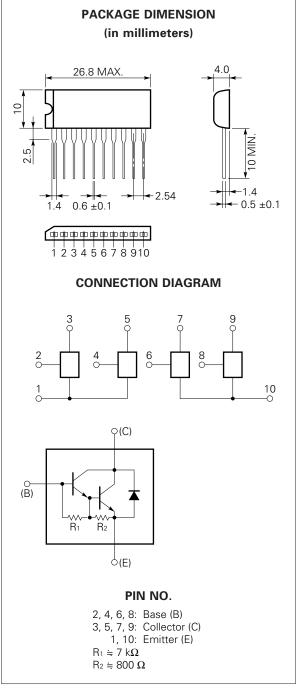
Part Number	Package	Quality Grade		
μPA1436H	10 Pin SIP	Standard		

Please refer to "Quality grade on NEC Semiconductor Device" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

	Collector to Base Voltage	Vсво	150	V
Collector to Emitter Voltage		Vceo	100	V
Emitter to Base Voltage		Vево	7	V
Collector Current (DC)		Ic(DC)	±3	A/unit
	Collector Current (pulse)	C(pulse)*	±6	A/unit
Base Current (DC)		IB(DC)	0.3	A/unit
Total Power Dissipation		PT1**	3.5	W
	(T _a = 25 °C)			
	Total Power Dissipation	PT2**	28	W
	$(T_c = 25 ^{\circ}C)$			
	Junction Temperature	T_{j}	150	°C
	Storage Temperature	T _{stg} -55	to +150	°C
	* PW \leq 350 μ s, Duty Cycle \leq	10 %		

^{** 4} Circuits



The information in this document is subject to change without notice.

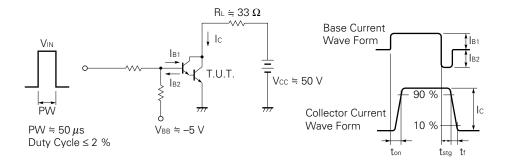


ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector to Emitter Sustaining Voltage	VCEO(sus)	100			V	lc = 1.5 A, l _B = 1.5 mA, L = 1 mH
Collector Leakage Current	Ісво			10	μΑ	Vcb = 100 V, IE = 0
Emitter Leakage Current	Ієво			1	mA	VEB = 5 V, Ic = 0
DC Current Gain	h _{FE1} *	1000			_	Vce = 2 V, Ic = 0.5 A
DC Current Gain	h _{FE2} *	2000	7000	20000	_	Vce = 2 V, Ic = 1.5 A
Collector Saturation Voltage	V _{CE(sat)} *		0.9	1.2	V	Ic = 1.5 A, I _B = 1.5 mA
Base Saturation Voltage	V _{BE(sat)} *		1.5	2	V	Ic = 1.5 A, I _B = 1.5 mA
Turn On Time	ton		1		μs	Ic = 1.5 A
Storage Time	tstg		3		μs	l _{B1} = −l _{B2} = 1.5 mA Vcc ≒ 50 V, R _L ≒ 33 Ω
Fall Time	tf		1		μs	See test circuit

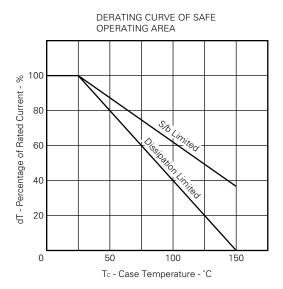
^{*} PW \leq 350 μ s, Duty Cycle \leq 2 % /pulsed

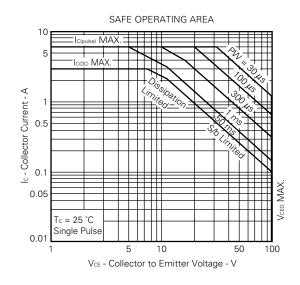
SWITCHING TIME TEST CIRCUIT

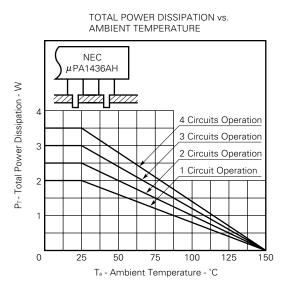


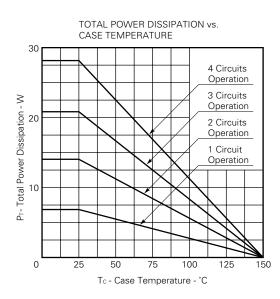


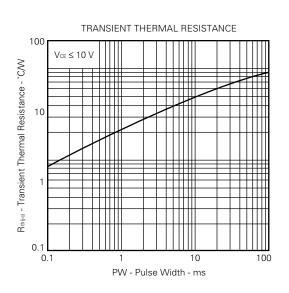
TYPICAL CHARACTERISTICS (Ta = 25 °C)

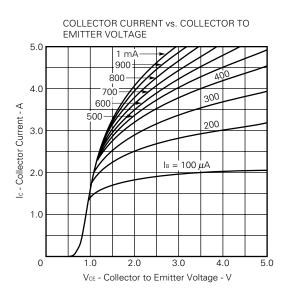




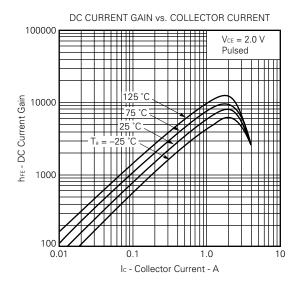


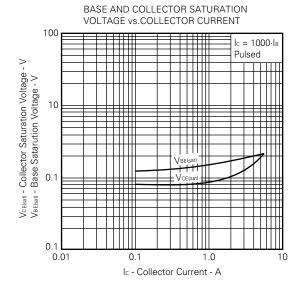














REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

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Application examples recommended by NEC Corporation

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.

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